

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$ $T_C = +25^\circ C$
30V	1.6m $\Omega$ @ $V_{GS} = 10V$	240A

## Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize  $R_{DS(ON)}$ , yet maintain superior switching performance. This device is ideal for use in power management and load switch.

## Applications

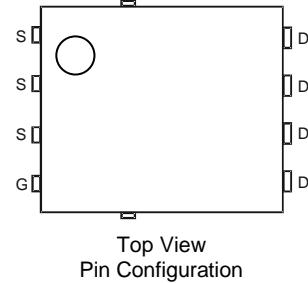
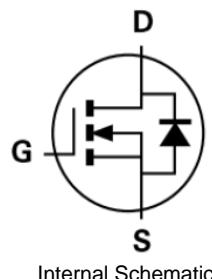
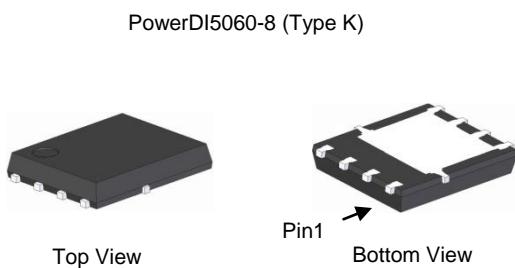
- DC-DC Converters
- Load Switch

## Features

- Thermally Efficient Package – Cooler Running Applications
- <1.1mm Package Profile – Ideal for Thin Applications
- High Conversion Efficiency
- Low  $R_{DS(ON)}$  – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: PowerDI<sup>®</sup>5060-8 (Type K)
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208<sup>(e3)</sup>
- Weight: 0.097 grams (Approximate)



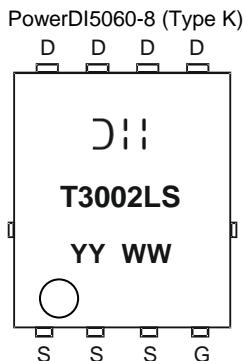
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3002LPS-13	PowerDI5060-8 (Type K)	2,500/Tape & Reel

Notes:

- EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



DII = Manufacturer's Marking  
T3002LS = Product Type Marking Code  
YYWW = Date Code Marking  
YY = Last Two Digits of Year (ex: 17 = 2017)  
WW = Week Code (01 to 53)

**Maximum Ratings** (@ $T_C = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 16$	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 7)	Steady State	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	$I_D$	240 240	A
Maximum Continuous Body Diode Forward Current (Note 7)			$I_S$	100	A
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)			$I_{DM}$	400	A
Pulsed Continuous Body Diode Forward Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)			$I_{SM}$	400	A
Avalanche Current, $L=3\text{mH}$ (Note 8)			$I_{AS}$	15	A
Avalanche Energy, $L=3\text{mH}$ (Note 8)			$E_{AS}$	700	mJ

**Thermal Characteristics** (@ $T_C = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	$P_D$	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	103	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$	$P_D$	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	51	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 7)	$T_C = +25^\circ\text{C}$	$P_D$	136	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.1	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$		-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_C = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 9)						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS</b> (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	2	V	$V_{DS} = V_{GS}, I_D = 1\text{mA}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.25	1.6	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 25\text{A}$
		—	2	2.5		$V_{GS} = 4.5\text{V}, I_D = 25\text{A}$
Diode Forward Voltage	$V_{SD}$	—	0.8	1.1	V	$V_{GS} = 0\text{V}, I_S = 25\text{A}$
<b>DYNAMIC CHARACTERISTICS</b> (Note 10)						
Input Capacitance	$C_{ISS}$	—	5,000	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	$C_{OSS}$	—	2,660	—		
Reverse Transfer Capacitance	$C_{RSS}$	—	300	—		
Gate Resistance	$R_G$	—	0.75	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_G$	—	37	—	nC	$V_{DS} = 15\text{V}, I_D = 25\text{A}$
Total Gate Charge ( $V_{GS} = 10\text{V}$ )	$Q_G$	—	77	—		
Gate-Source Charge	$Q_{GS}$	—	10	—		
Gate-Drain Charge	$Q_{GD}$	—	14	—	ns	$V_{DD} = 15\text{V}, V_{GS} = 4.5\text{V}, I_D = 25\text{A}, R_G = 4.7\Omega$
Turn-On Delay Time	$t_{D(ON)}$	—	21	—		
Turn-On Rise Time	$t_R$	—	45	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	32	—		
Turn-Off Fall Time	$t_F$	—	26	—		
Body Diode Reverse Recovery Time	$t_{RR}$	—	44	—	ns	$I_S = 15\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	$Q_{RR}$	—	52	—	nC	

Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- Thermal resistance from junction to soldering point (on the exposed drain pad).
- $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^\circ\text{C}$ .
- Short duration pulse test used to minimize self-heating effect.
- Guaranteed by design. Not subject to product testing.

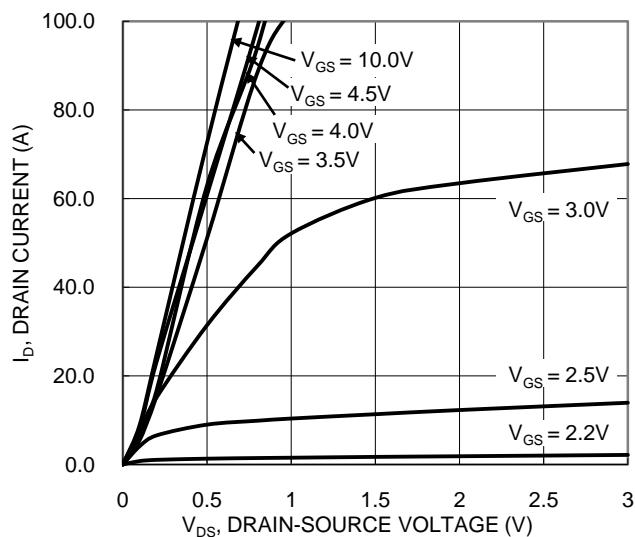


Figure 1. Typical Output Characteristic

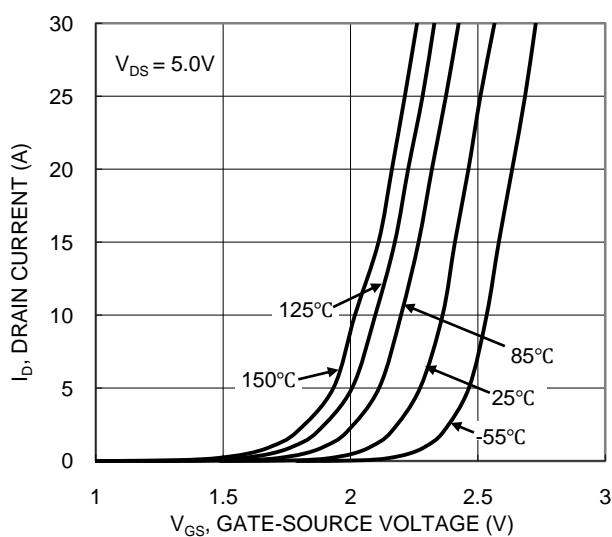


Figure 2. Typical Transfer Characteristic

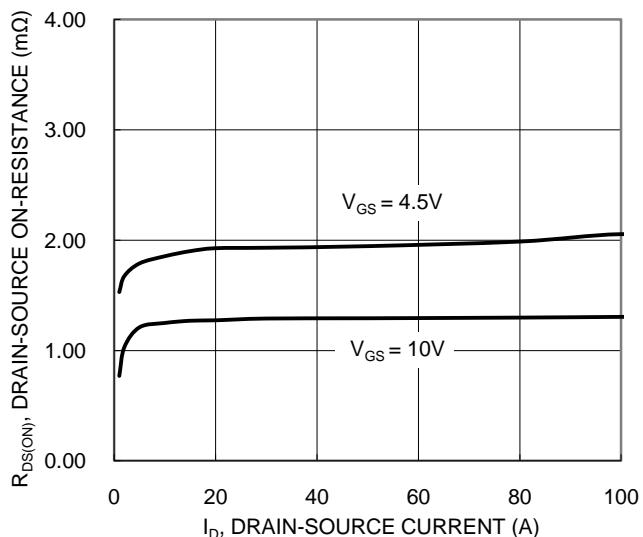


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

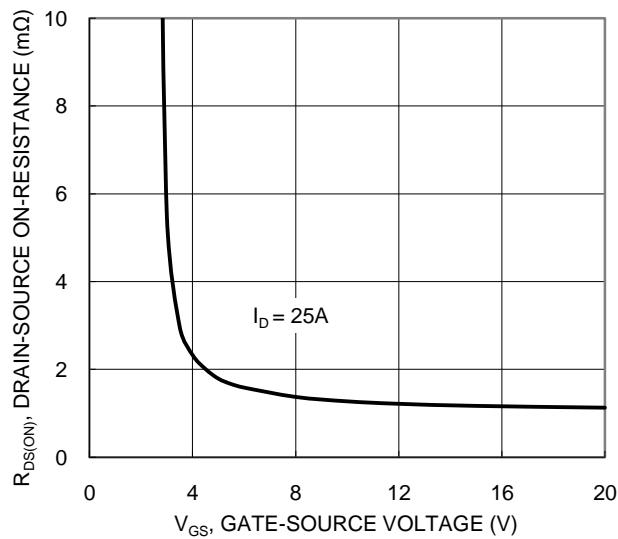


Figure 4. Typical Transfer Characteristic

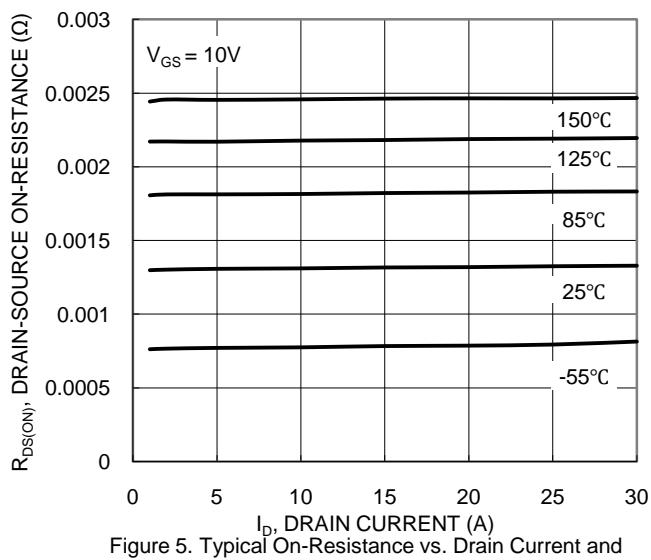


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

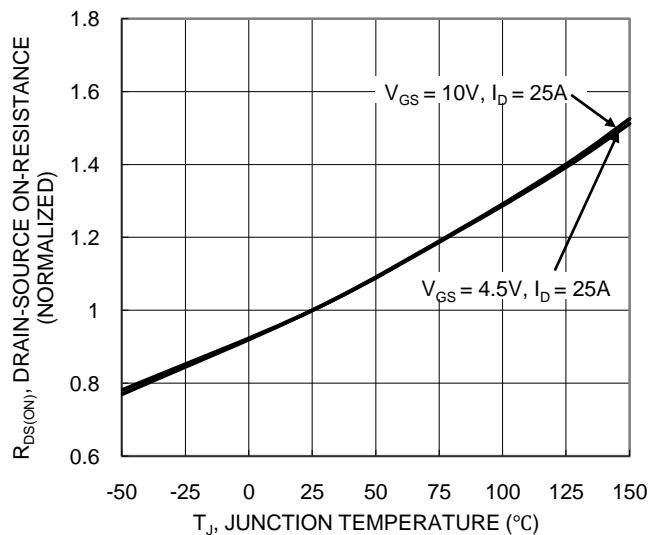
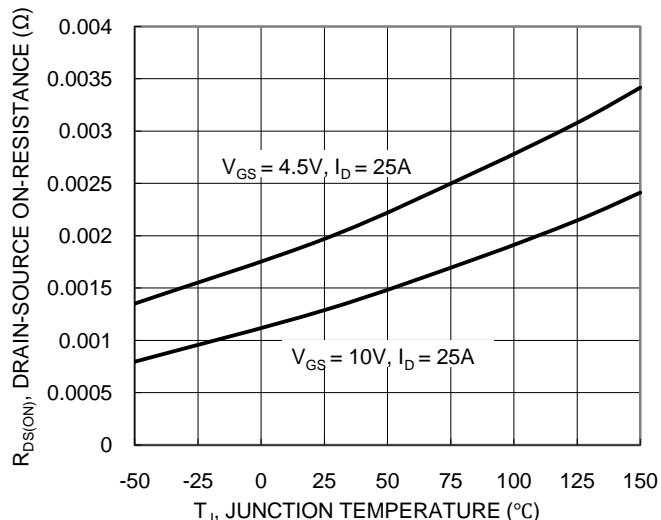
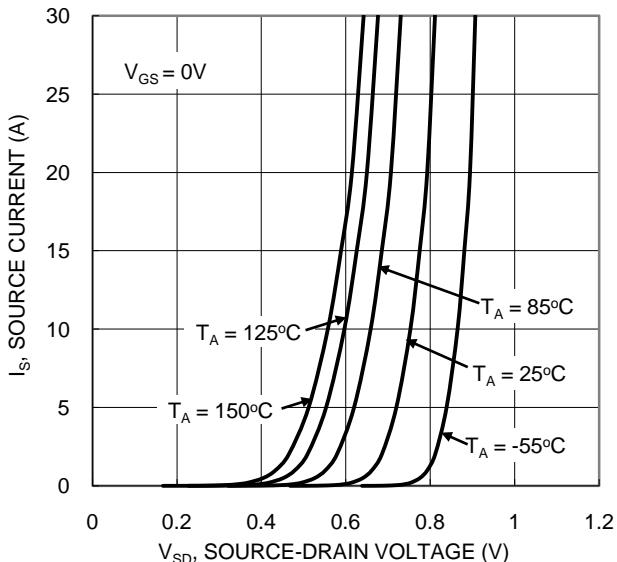


Figure 6. On-Resistance Variation with Temperature

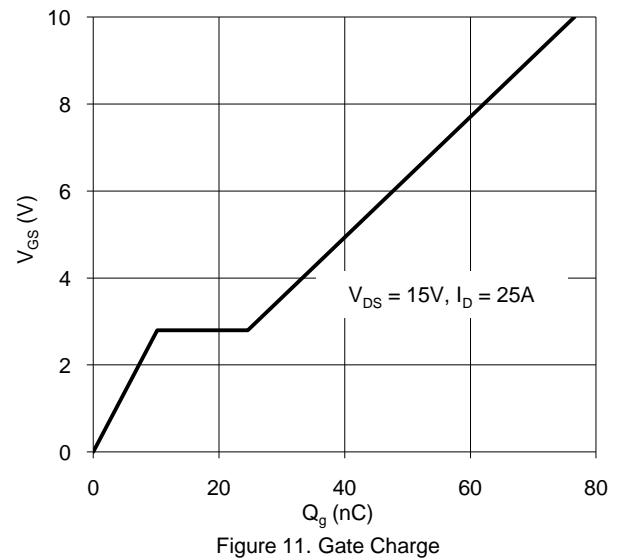


$V_{GS} = 4.5V, I_D = 25A$

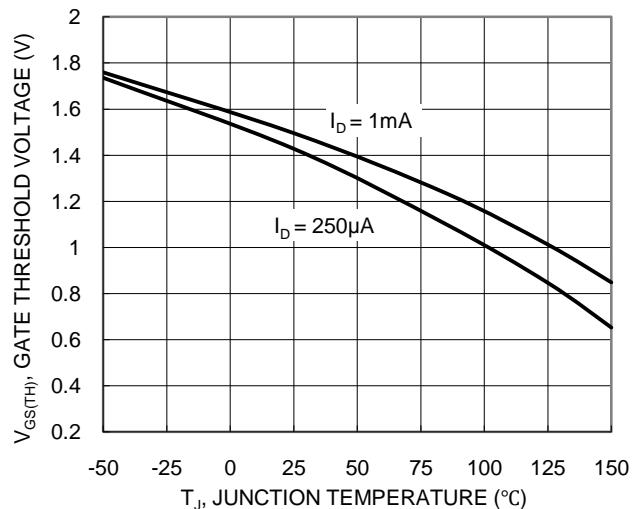
$V_{GS} = 10V, I_D = 25A$



$V_{GS} = 0V$

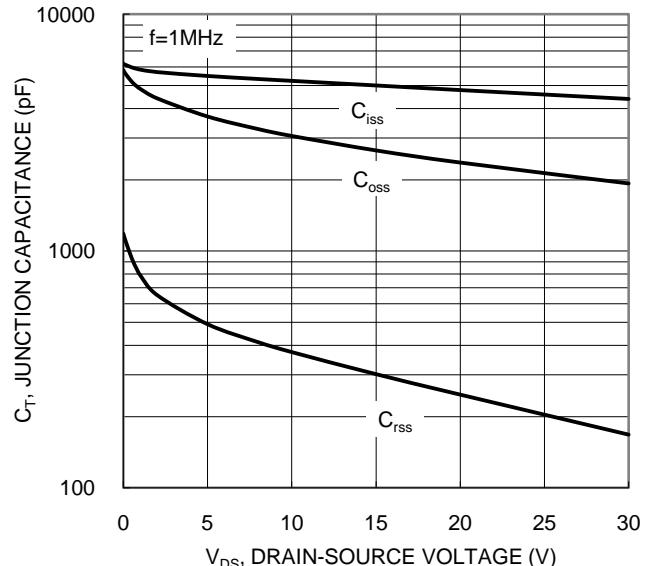


$V_{DS} = 15V, I_D = 25A$

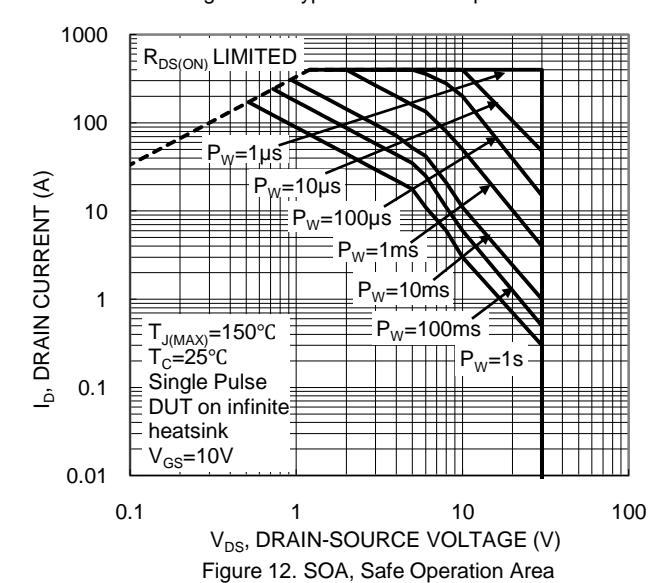


$I_D = 1mA$

$I_D = 250\mu A$



$f=1MHz$



$T_{J(MAX)} = 150^\circ C$   
 $T_C = 25^\circ C$   
 Single Pulse  
 DUT on infinite  
 heatsink  
 $V_{GS} = 10V$

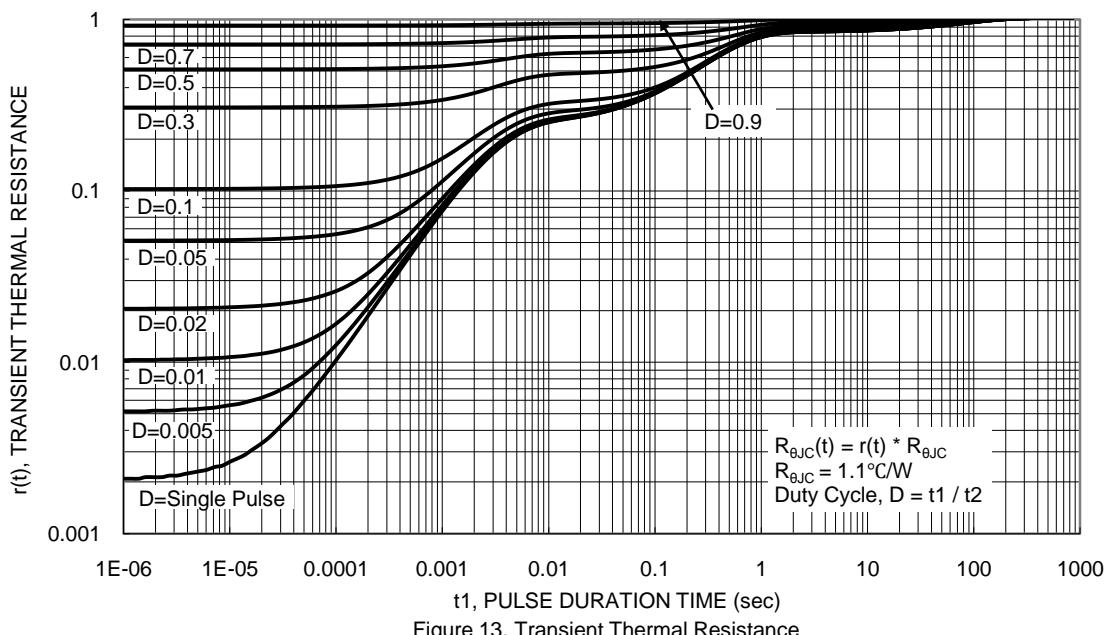
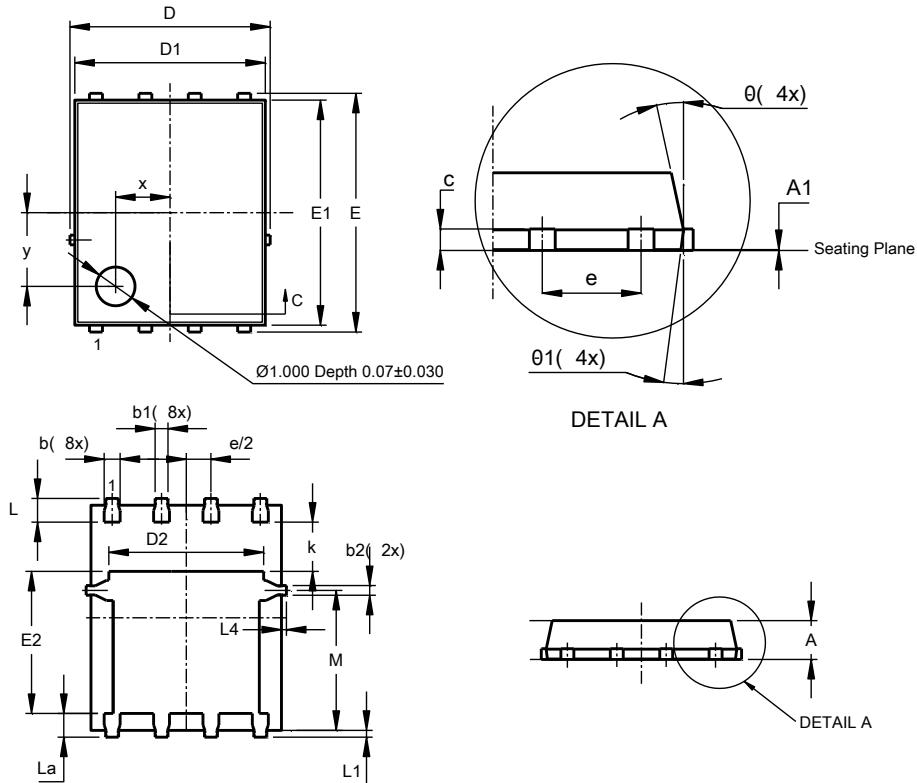


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)

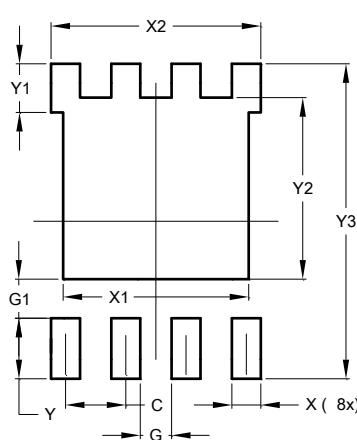


PowerDI5060-8 (Type K)			
Dim	Min	Max	Typ
<b>A</b>	0.90	1.10	1.00
<b>A1</b>	0	0.05	0.02
<b>b</b>	0.33	0.51	0.41
<b>b1</b>	0.300	0.366	0.333
<b>b2</b>	0.20	0.35	0.25
<b>c</b>	0.23	0.33	0.277
<b>D</b>	5.15 BSC		
<b>D1</b>	4.85	4.95	4.90
<b>D2</b>	-	-	3.98
<b>E</b>	6.15 BSC		
<b>E1</b>	5.75	5.85	5.80
<b>E2</b>	3.56	3.725	3.66
<b>E</b>	1.27BSC		
<b>k</b>	-	-	1.27
<b>L</b>	0.51	0.71	0.61
<b>La</b>	0.51	0.675	0.61
<b>L1</b>	0.05	0.20	0.175
<b>L4</b>	-	-	0.125
<b>M</b>	3.50	3.71	3.605
<b>x</b>	-	-	1.400
<b>y</b>	-	-	1.900
<b>θ</b>	10°	12°	11°
<b>θ1</b>	6°	8°	7°
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)
<b>C</b>	1.270
<b>G</b>	0.660
<b>G1</b>	0.820
<b>X</b>	0.610
<b>X1</b>	3.910
<b>X2</b>	4.420
<b>Y</b>	1.270
<b>Y1</b>	1.020
<b>Y2</b>	3.810
<b>Y3</b>	6.610

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